

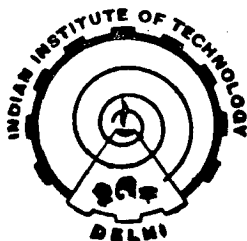
**RESONANT RAMAN SCATTERING
IN
III-V ALLOY SEMICONDUCTORS**

by

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Thesis submitted in fulfillment of the
requirements of the degree of
DOCTOR OF PHILOSOPHY



to the

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CERTIFICATE

This is to certify that the thesis entitled "Resonant Raman Scattering in III-V alloy semiconductors" which is being submitted by Mr. Ravi Kant Soni to the Indian Institute of Technology, New Delhi is a record of bonafide research work carried out by him under our guidance and supervision.

In our opinion this thesis has reached the standard fulfilling the requirements of all regulations relating to the degree. The results contained in it have not been submitted in part or in full to any other university or Institute for the award of any degree or diploma.



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